<table>
<thead>
<tr>
<th>Authors</th>
<th>Title</th>
<th>Journal</th>
<th>Volume</th>
<th>Issue</th>
<th>Pages</th>
</tr>
</thead>
<tbody>
<tr>
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<td>79</td>
<td></td>
<td>344 – 346</td>
</tr>
<tr>
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<td>1</td>
<td></td>
<td>327 – 332</td>
</tr>
<tr>
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<td>146 – 153</td>
</tr>
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<td>J. Appl. Phys.</td>
<td>90</td>
<td></td>
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</tr>
<tr>
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<td>Morphology and solubility of multiple crystal forms of Taka-amylase A</td>
<td>J. Cryst. Growth</td>
<td>222</td>
<td></td>
<td>311 – 316</td>
</tr>
<tr>
<td>Azuma, Y; Usami, N; Ujihara, T; Sazaki, G; Murakami, Y; Miyashita, S; Fujiwara, K; Nakajima, K</td>
<td>Growth of SiGe bulk crystal with uniform composition by directly controlling the growth temperature at the crystal–melt inter–face using in situ monitoring system</td>
<td>J. Cryst. Growth</td>
<td>224</td>
<td></td>
<td>204 – 211</td>
</tr>
<tr>
<td>Shimomura, S; Kitano, Y; Kuge, H; Kitada, T; Nakajima, K; Hiyamizu, S</td>
<td>Lattice–matched InxGa1–xAs/InxAl1–xAs quantum wells (x=0.18 and 0.19) grown on (411)A– and (100)–oriented InGaAs ternary substrates by molecular beam epitaxy</td>
<td>J. Cryst. Growth</td>
<td>227</td>
<td></td>
<td>72 – 76</td>
</tr>
<tr>
<td>Usami, N; Miura, M; Ito, Y; Araki, Y; Nakajima, K; Shiraki, Y</td>
<td>Modification of the growth mode of Ge on Si(100) in the presence of buried Ge islands</td>
<td>J. Cryst. Growth</td>
<td>227</td>
<td></td>
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</tr>
<tr>
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<td>Crystal growth and structural properties of RRh3B2 (R = Gd, Er, Tm) compounds</td>
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<td>229</td>
<td></td>
<td>521 – 526</td>
</tr>
</tbody>
</table>

| IMR Number | 01-IMR0024 | 01-IMR0025 | 01-IMR0026 | 01-IMR0027 | 01-IMR0028 | 01-IMR0029 | 01-IMR0030 | 01-IMR0031 | 01-IMR0032 |
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